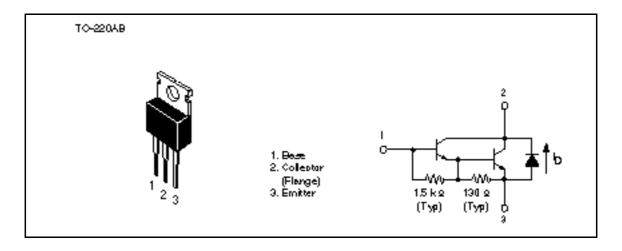
Silicon NPN Triple Diffused

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Application

Power switching

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

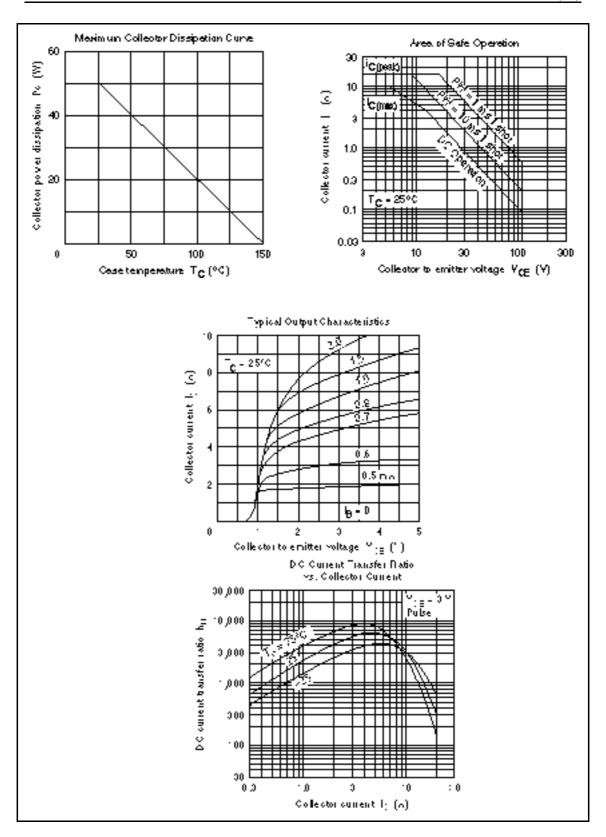
Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	120	V	
Collector to emitter voltage	V_{CEO}	120	V	
Emitter to base voltage	V_{EBO}	7	V	
Collector current	I _c	10	А	
Collector peak current	I _{C(peak)}	15	А	
Collector power dissipation	P _c *1	50	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	
C to E diode forward current	I _D	10	А	

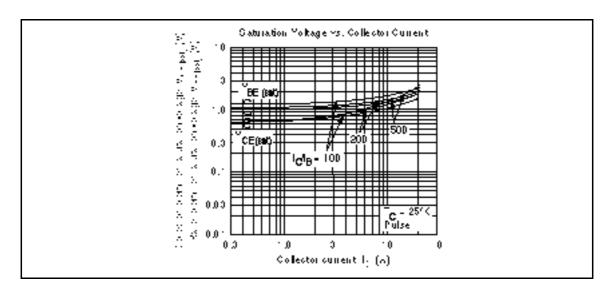
Note: 1. Value at $T_c = 25$ °C.

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	_	_	V	$I_C = 25 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	_	_	V	$I_{E} = 200 \text{ mA}, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	100	μΑ	$V_{CB} = 120 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	10	μΑ	$V_{CE} = 100 \text{ V}, R_{BE} =$
DC current transfer ratio	h _{FE}	1000	_	2000		$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ A}^{*1}$
Collector to emitter saturation	$V_{\text{CE(sat)1}}$	_	_	1.5	V	$I_{\rm C} = 5 \text{ A}, I_{\rm B} = 10 \text{ mA}^{*1}$
voltage	$V_{\text{CE(sat)2}}$	_	_	3.0	V	$I_{\rm C} = 10 \text{ A}, I_{\rm B} = 0.1 \text{ A}^{*1}$
Base to emitter saturation	$V_{BE(sat)1}$	_	_	2.0	V	$I_{\rm C} = 5 \text{ A}, I_{\rm B} = 10 \text{ mA}^{*1}$
voltage	$V_{BE(sat)2}$	_	_	3.5	V	$I_{\rm C} = 10 \text{ A}, I_{\rm B} = 0.1 \text{ A}^{*1}$
C to E diode forward voltage	$V_{\scriptscriptstyle D}$	_	_	3.0	V	$I_D = 10 A^{*1}$
Turn on time	t _{on}	_	0.8	_	μs	$I_{\rm C} = 5 \text{ A}, I_{\rm B1} = -I_{\rm B2} = 10 \text{ mA}$
Turn off time	t _{off}	_	8.0	_	μs	_

Note: 1. Pulse test.





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